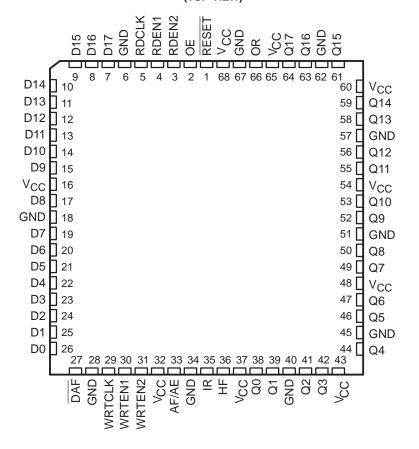
CLOCKED FIRST-IN, FIRST-OUT MEMORY

SCAS151C - JANUARY 1991 - REVISED FEBRUARY 1996

- Member of the Texas Instruments Widebus™ Family
- Independent Asynchronous Inputs and Outputs
- 1024 Words × 18 Bits
- Read and Write Operations Can Be Synchronized to Independent System Clocks
- Programmable Almost-Full/Almost-Empty Flag
- Pin-to-Pin Compatible With SN74ACT7881, SN74ACT7882, and SN74ACT7884

- Input-Ready, Output-Ready, and Half-Full Flags
- Cascadable in Word Width and/or Word Depth
- Fast Access Times of 15 ns With a 50-pF Load
- High-Output Drive for Direct Bus Interface
- Available in 68-Pin PLCC (FN) and Space-Saving 80-Pin Thin Quad Flat (PN) Packages

FN PACKAGE (TOP VIEW)



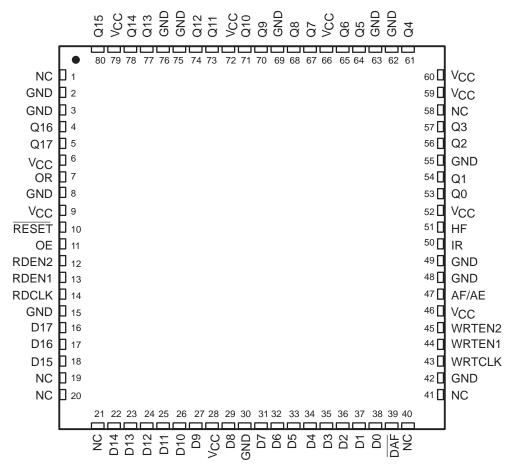


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Widebus is a trademark of Texas Instruments Incorporated.



PN PACKAGE (TOP VIEW)



NC - No internal connection

description

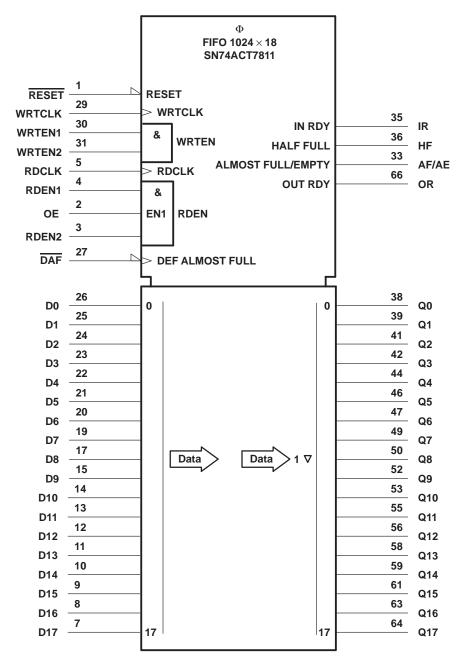
A FIFO memory is a storage device that allows data to be written into and read from its array at independent data rates. The SN74ACT7811 is a 1024×18 -bit FIFO for high speed and fast access times. It processes data at rates up to 40 MHz and access times of 15 ns in a bit-parallel format. Data outputs are noninverting with respect to the data inputs. Expansion is easily accomplished in both word width and word depth.

The SN74ACT7811 has normal input-bus-to-output-bus asynchronous operation. The special enable circuitry adds the ability to synchronize independent read and write (interrupts or requests) to their respective system clock.

The SN74ACT7811 is characterized for operation from 0°C to 70°C.



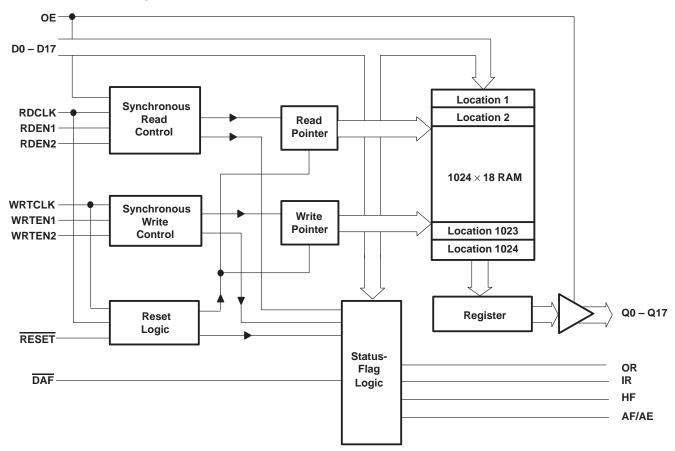
logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for the FN package.

CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS151C – JANUARY 1991 – REVISED FEBRUARY 1996

functional block diagram





CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS151C – JANUARY 1991 – REVISED FEBRUARY 1996

Terminal Functions

TERMINAL [†]		l						
NAME	NO.	1/0	DESCRIPTION					
AF/AE	33	0	Almost-full/almost-empty flag. The AF/AE boundary is defined by the almost-full/almost-empty offset value (X). This value can be programmed during reset or the default value of 256 can be used. AF/AE is high when the FIFO contains (X + 1) or less words or (1025 – X) or more words. AF/AE is low when the FIFO contains between (X + 2) and (1024 - X) words. Programming procedure for AF/AE – The almost-full/almost-empty flag is programmed during each reset cycle. The almost-full/almost-empty offset value (X) is either a user-defined value or the default of X = 256. Instructions to program AF/AE using both methods are as follows: User-defined X Step 1: Take DAF from high to low. Step 2: If RESET is not already low, take RESET low. Step 3: With DAF held low, take RESET high. This defines the AF/AE using X. Step 4: To retain the current offset for the next reset, keep DAF low.					
			Default X To redefine AF/AE using the default value of $X = 256$, hold \overline{DAF} high during the reset cycle.					
DAF	27	ı	Define almost full. The high-to-low transition of \overline{DAF} stores the binary value of data inputs as the almost-full/almost-empty offset value (X). With \overline{DAF} held low, a low pulse on \overline{RESET} defines the AF/AE flag using X.					
D0-D17	26-19, 17, 15-7	ı	Data inputs for 18-bit-wide data to be stored in the memory. Data lines $D0-D8$ also carry the almost-full/almost-empty offset value (X) on a high-to-low transition of the \overline{DAF} .					
HF	36	0	Half-full flag. HF is high when the FIFO contains 513 or more words and is low when it contains 512 or less words.					
IR	35	0	Input-ready flag. IR is high when the FIFO is not full and low when the device is full. During reset, IR is driven low on the rising edge of the second WRTCLK pulse. IR is then driven high on the rising edge of the second WRTCLK pulse after RESET goes high. After the FIFO is filled and IR is driven low, IR is driven high on the second WRTCLK pulse after the first valid read.					
OE	2	ı	Output enable. The data-out (Q0-Q17) outputs are in the high-impedance state when OE is low. OE must be high before the rising edge of RDCLK to read a word from memory.					
OR	66	0	Output-ready flag. OR is high when the FIFO is not empty and low when it is empty. During reset, OR is set low on the rising edge of the third RDCLK pulse. OR is set high on the rising edge of the third RDCLK pulse to occur after the first word is written into the FIFO. OR is set low on the rising edge of the first RDCLK pulse after the last word is read.					
Q0-Q17	38-39, 41-42, 44, 46-47, 49-50, 52-53, 55-56, 58-59, 61, 63-64	0	Data outputs. The first data word to be loaded into the FIFO is moved to Q0-Q17 on the rising edge of the third RDCLK pulse to occur after the first valid write. The RDEN1 and RDEN2 inputs do not affect this operation. Following data is unloaded on the rising edge of RDCLK when RDEN1, RDEN2, OE, and the OR are high.					
RDCLK	5	ı	Read clock. Data is read out of memory on a low-to-high transition RDCLK if OR, OE, and RDEN1 and RDEN2 control inputs are high. RDCLK is a free-running clock and functions as the synchronizing clock for all data transfers out of the FIFO. OR is also driven synchronously with respect to RDCLK.					
RDEN1, RDEN2	4 3	I	Read enable. RDEN1 and RDEN2 must be high before a rising edge on RDCLK to read a word out of memory. RDEN1 and RDEN2 are not used to read the first word stored in memory.					
RESET	1	I	A reset is accomplished by taking $\overline{\text{RESET}}$ low and generating a minimum of four RDCLK and WRTCLK cycles. This ensures that the internal read and write pointers are reset and OR, HF, and IR are low and AF/AE is high. The FIFO must be reset upon power up. With $\overline{\text{DAF}}$ at a low level, a low pulse on $\overline{\text{RESET}}$ defines the AF/AE status flag using the almost-full/almost-empty offset value (X), where X is the value previously stored. With $\overline{\text{DAF}}$ at a high level, a low-level pulse on $\overline{\text{RESET}}$ defines the AF/AE flag using the default value of X = 256.					

[†] Terminals listed are for the FN package.



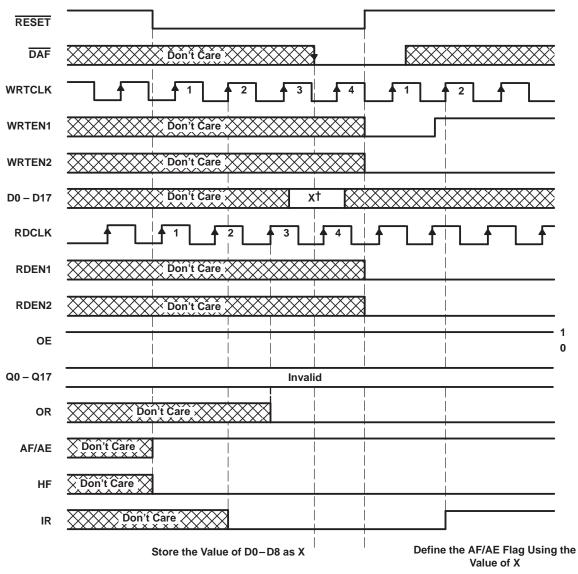
CLOCKED FIRST-IN, FIRST-OUT MEMORY

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Terminal Functions (Continued)

TERM	TERMINAL [†]		DESCRIPTION			
NAME	NO.	1/0	DESCRIPTION			
WRTCLK	29	ı	Write clock. Data is written into memory on a low-to-high transition of WRTCLK if IR, WRTEN1, and WRTEN2 are high. WRTCLK is a free-running clock and functions as the synchronizing clock for all data transfers into the FIFO. IR is also driven synchronously with respect to WRTCLK.			
WRTEN1, WRTEN2	30 31	1	Write enables. WRTEN1 and WRTEN2 must be high before a rising edge on WRTCLK for a word to be written into memory. WRTEN1 and WRTEN2 do not affect the storage of the almost-full/almost-empty offset value (X).			

[†] Terminals listed are for the FN package.



[†] X is the binary value of D0-D8 only.

Figure 1. Reset Cycle: Define AF/AE Using the Value of X



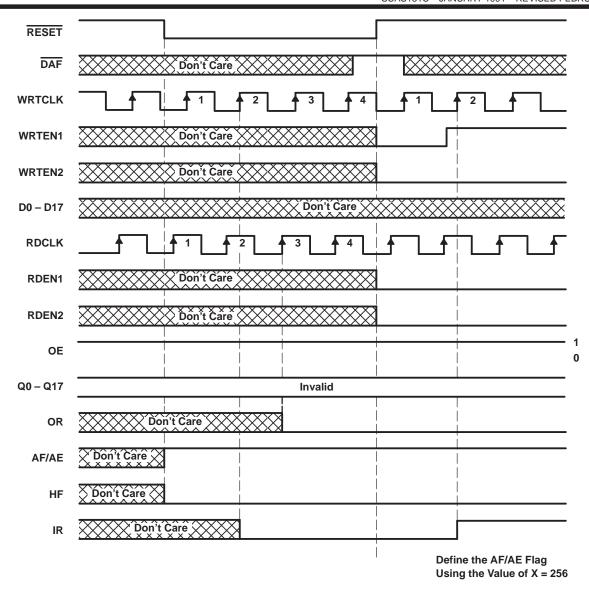


Figure 2. Reset Cycle: Define AF/AE Using the Default Value



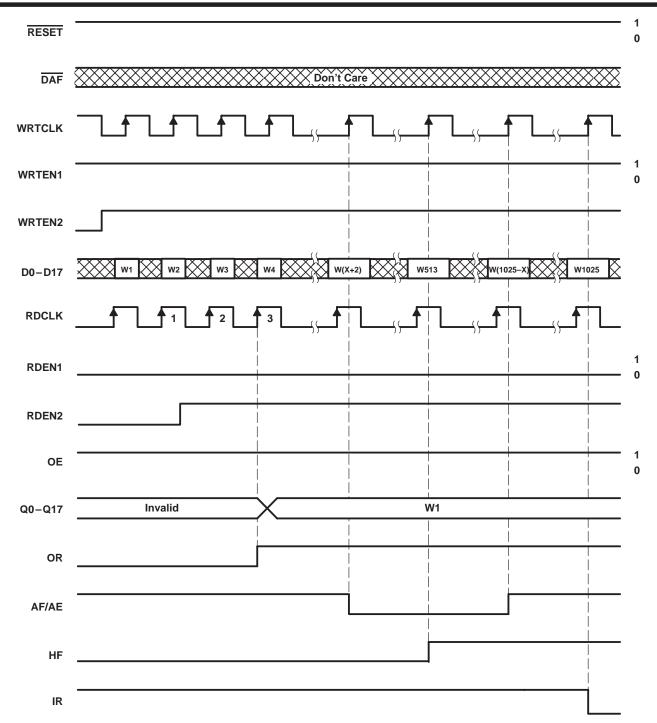


Figure 3. Write Cycle



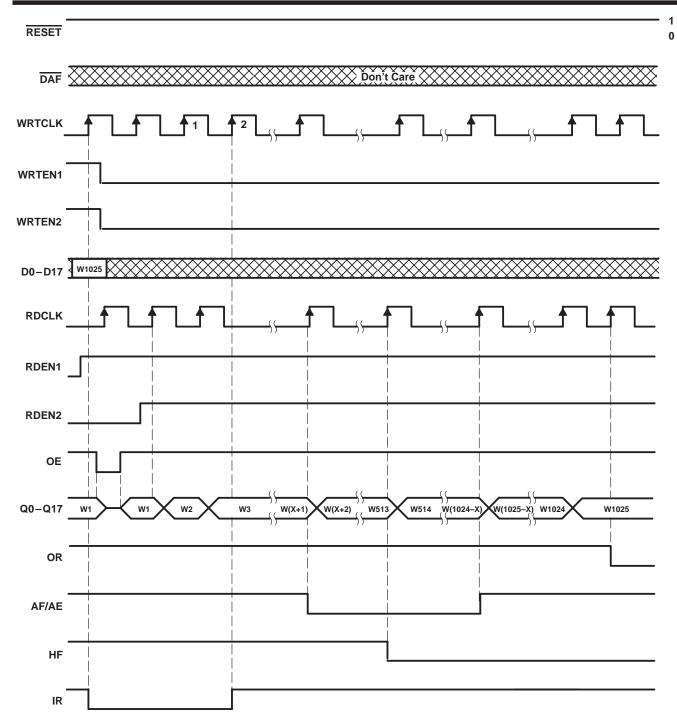


Figure 4. Read Cycle



CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS151C – JANUARY 1991 – REVISED FEBRUARY 1996

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage range, V _{CC}	0.5 V to 7 V
Input voltage, V _I	7 V
Voltage applied to a disabled 3-state output	5.5 V
Operating free-air temperature range, T _A	0°C to 70°C
Storage temperature range, T _{stg}	−65°C to 150°C

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

recommended operating conditions

		MIN	MAX	UNIT
VCC	Supply voltage	4.5	5.5	V
VIH	High-level input voltage	2		V
V _{IL}	Low-level input voltage		0.8	V
IOH	High-level output current		-8	mA
l _{OL}	Low-level output current		16	mA
TA	Operating free-air temperature	0	70	°C

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	TYP [‡]	MAX	UNIT	
Voн	$V_{CC} = 4.5 \text{ V},$	$I_{OH} = -8 \text{ mA}$	2.4			V
V _{OL}	$V_{CC} = 4.5 \text{ V},$	$I_{OL} = 16 \text{ mA}$			0.5	V
lį	V _{CC} = 5.5 V,	VI = VCC or 0 V			±5	μΑ
loz	V _{CC} = 5.5 V,	VO =VCC or 0 V			±5	μΑ
. 2	$V_{I} = V_{CC} - 0.2 \text{ V or } 0 \text{ V}$				400	μΑ
I _{CC} §	One input at 3.4 V,	Other inputs at V _{CC} or GND			1	mA
C _i	V _I = 0 V, f = 1 MHz			4		pF
Co	V _O = 0 V, f = 1 MHz			8		pF

[‡] All typical values are at $V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$.



[§] I_{CC} tested with outputs open

CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS151C – JANUARY 1991 – REVISED FEBRUARY 1996

timing requirements (see Figures 1 through 8)

			'ACT78	311-15	′ACT78	311-18	'ACT78	311-20	'ACT78	311-25	UNIT	
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	UNII	
f _{clock}	Clock frequency		40		35		28.5		16.7		MHz	
ICIOCK CIOCK HEQUEIN		D0-D17 high or low	10		12		14		20			
		WRTCLK high	7		8.5		10		17			
		WRTCLK low	10		11		14		23			
		RDCLK high	7		8.5		10		17			
t _w	Pulse duration	RDCLK low	10		11		14		23		ns	
-vv		DAF high	10		10		10		10			
		WRTEN1, WRTEN2 high or low	10		10		10		10			
		OE, RDEN1, RDEN2 high or low	10		10		10		10			
		D0-D17 before WRTCLK↑	5		5		5		5			
		WRTEN1, WRTEN2 high before WRTCLK↑	5		5		5		5			
		OE, RDEN1, RDEN2 high before RDCLK↑	5		5		5		5			
t _{su}	Setup time	Reset: RESET low before first WRTCLK and RDCLK↑	7		7		7		7		ns	
		Define AF/AE: D0−D8 before DAF↓	5		5		5		5			
		Define AF/AE: DAF↓ before RESET↑	7		7		7		7			
		Define AF/AE (default): DAF high before RESET↑	5		5		5		5			
		D0-D17 after WRTCLK↑	1		1		1		1			
		WRTEN1, WRTEN2 high after WRTCLK↑	1		1		1		1			
		OE, RDEN1, RDEN2 high after RDCLK↑	1		1		1		1			
^t h	Hold time	Reset: RESET low after fourth WRTCLK and RDCLK↑	0		0		0		0		ns	
		Define AF/AE: D0−D8 after DAF↓	1		1		1		1			
		Define AF/AE: DAF low after RESET↑	0		0		0		0			
		Define AF/AE (default): DAF high after RESET↑	1		1		1		1			

[†] To permit the clock pulse to be utilized for reset purposes

CLOCKED FIRST-IN, FIRST-OUT MEMORY SCAS151C – JANUARY 1991 – REVISED FEBRUARY 1996

switching characteristics over recommended operating free-air temperature range (see Figures 9 and 10)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V_{CC} = 4.5 V to 5.5 V, C_L = 50 pF, R_L = 500 Ω, T_A = 0°C to 70°C									UNIT
	, ,	, ,	′AC	T7811-1	15	'ACT78	311-18	'ACT78	311-20	'ACT7811-25		
			MIN	TYP	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
f _{max}	WRTCLK or RDCLK		40			35		28.5		16.7		MHz
t _{pd}		Any 0	4	12	15	4	18	4	20	4	25	
t _{pd} †	RDCLK↑	Any Q		10.5								ns
^t pd	WRTCLK↑	IR	2		10	2	12	2	14	2	16	ns
tpd	RDCLK↑	OR	2		10	2	12	2	14	2	16	ns
	WRTCLK↑	AF/AE	6		20	6	22	6	24	6	26	no
^t pd	RDCLK↑	AF/AE	6		20	6	22	6	24	6	26	ns
t _{PLH}	WRTCLK↑	HF	6		19	6	21	6	23	6	25	
t _{PHL}	RDCLK↑	ПГ	6		19	6	21	6	23	6	25	ns
t _{PLH}	DECET	AF/AE	3		19	3	21	3	23	3	25	no
^t PHL	RESET↓	HF	4		21	4	23	4	25	4	27	ns
t _{en}	OE	Any O	2		11	2	11	2	11	2	11	ne
t _{dis}	OE .	Any Q	2		14	2	14	2	14	2	14	ns

[†] This parameter is measured with $C_L = 30 \text{ pF}$ (see Figure 5).

operating characteristics, V_{CC} = 5 V, T_A = 25°C

	PARAMETER	TEST CONDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance per 1K bits	$C_L = 50 \text{ pF}, f = 5 \text{ MHz}$	65	pF



TYPICAL CHARACTERISTICS

TYPICAL PROPAGATION DELAY TIME

LOAD CAPACITANCE V_{CC} = 5 V $T_A = 25^{\circ}C$ $R_L = 500 \Omega$ tpd - Propagation Delay Time - ns C_L-Load Capacitance - pF

Figure 5



TYPICAL CHARACTERISTICS

TYPICAL POWER DISSIPATION CAPACITANCE

SUPPLY VOLTAGE

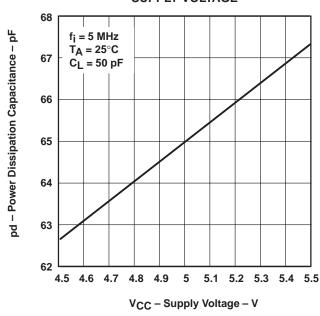


Figure 6

calculating power dissipation

The maximum power dissipation (P_T) of the SN74ACT7811 can be calculated by:

$$\mathsf{P}_{\mathsf{T}} = \mathsf{V}_{\mathsf{CC}} \times [\mathsf{I}_{\mathsf{CC}} + (\mathsf{N} \times \Delta \mathsf{I}_{\mathsf{CC}} \times \mathsf{dc})] + \Sigma \; (\mathsf{C}_{\mathsf{pd}} \times \mathsf{V}_{\mathsf{CC}}{}^2 \times \mathsf{f}_{\mathsf{i}}) + \Sigma \; (\mathsf{C}_{\mathsf{L}} \times \mathsf{V}_{\mathsf{CC}}{}^2 \times \mathsf{f}_{\mathsf{o}})$$

where:

power-down I_{CC} maximum Icc

number of inputs driven by a TTL device

 ΔI_{CC} = increase in supply current

= duty cycle of inputs at a TTL high level of 3.4 V

power dissipation capacitance

 $\begin{array}{c} C_{pd} \\ C_{L} \end{array}$ = output capacitive load = data input frequency data output frequency



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APPLICATION INFORMATION

expanding the SN74ACT7811

The SN74ACT7811 is expandable in width and depth. Expanding in word depth offers special timing considerations:

After the first data word is loaded into the FIFO, the word is unloaded and the output-ready flag (OR) output goes high after (N \times 3) read-clock (RDCLK) cycles, where N is the number of devices used in depth expansion.

After the FIFO is filled, the input-ready flag (IR) output goes low, the first word is unloaded, and the IR flag output is driven high after (N \times 2) write-clock cycles, where N is the number of devices used in depth expansion.

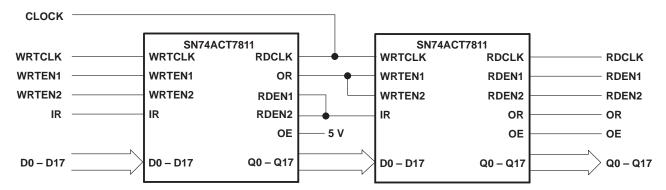


Figure 7. Word-Depth Expansion: 2048 Words \times 18 Bits, N = 2

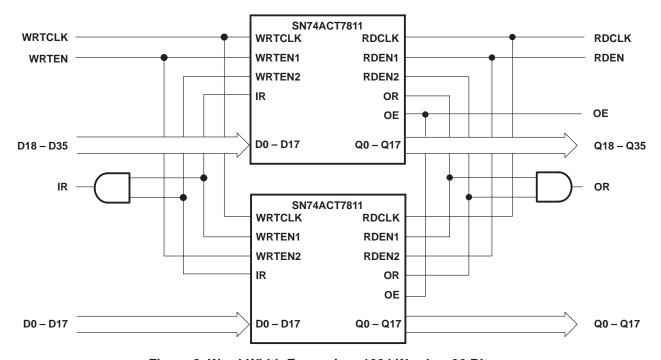


Figure 8. Word-Width Expansion: 1024 Words \times 36 Bits



PARAMETER MEASUREMENT INFORMATION

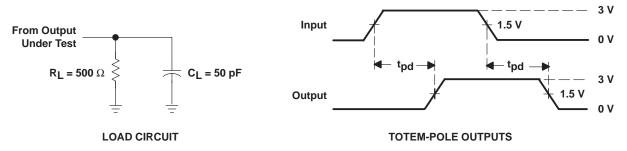
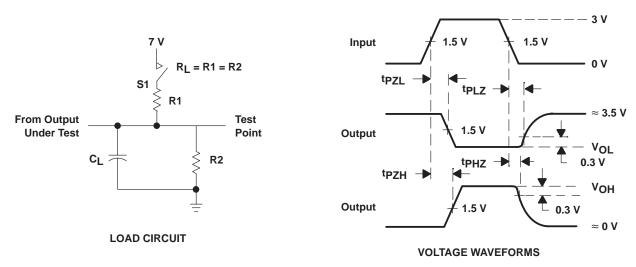


Figure 9. Standard CMOS Outputs



PARAMETER		R1, R2	C _L †	S1	
	^t PZH	500 Ω	50 pF	Open	
ten	tPZL	300 22	50 pr	Closed	
.	tPHZ	500 Ω	50 pF	Open	
^t dis	tPLZ	200 72	50 pF	Closed	
tpd		500 Ω	50 pF	Open	

[†] Includes probe and test fixture capacitance

Figure 10. 3-State Outputs (Any Q)







ti.com 6-Dec-2006

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins Pa	ckage Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
SN74ACT7811-15FN	OBSOLETE	PLCC	FN	68		TBD	Call TI	Call TI
SN74ACT7811-15PN	OBSOLETE	LQFP	PN	80		TBD	Call TI	Call TI
SN74ACT7811-18FN	OBSOLETE	PLCC	FN	68		TBD	Call TI	Call TI
SN74ACT7811-18FNR	OBSOLETE	PLCC	FN	68		TBD	Call TI	Call TI
SN74ACT7811-18PN	OBSOLETE	LQFP	PN	80		TBD	Call TI	Call TI
SN74ACT7811-20FN	NRND	PLCC	FN	68	18 (Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR
SN74ACT7811-20PN	OBSOLETE	LQFP	PN	80		TBD	Call TI	Call TI
SN74ACT7811-25FN	OBSOLETE	PLCC	FN	68		TBD	Call TI	Call TI
SN74ACT7811-25PN	OBSOLETE	LQFP	PN	80	•	TBD	Call TI	Call TI

 $^{(1)}$ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

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FN (S-PQCC-J**)

20 PIN SHOWN

PLASTIC J-LEADED CHIP CARRIER



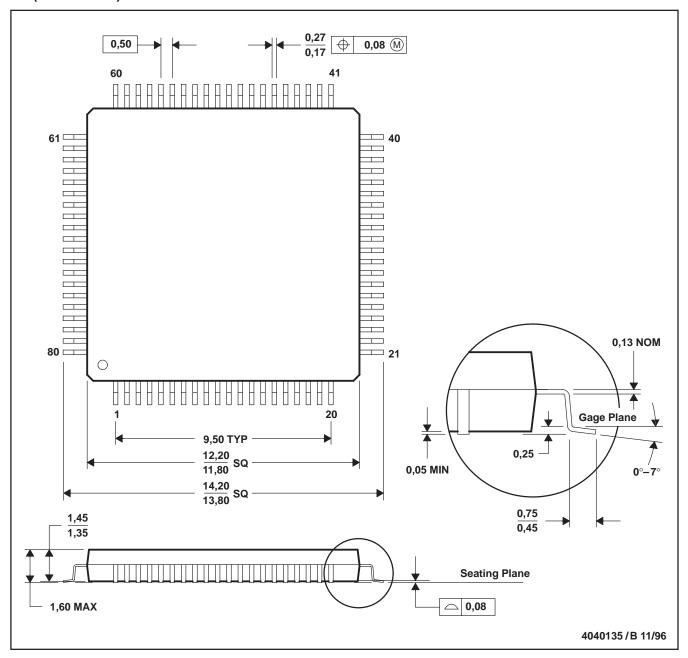
NOTES: A. All linear dimensions are in inches (millimeters).

- B. This drawing is subject to change without notice.
- C. Falls within JEDEC MS-018



PN (S-PQFP-G80)

PLASTIC QUAD FLATPACK



NOTES: A. All linear dimensions are in millimeters.

B. This drawing is subject to change without notice.

C. Falls within JEDEC MS-026

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